

Method for Removing Silicon Oxide Material Formed During Removal of Photoresist
TREATMENT ON SILICON OXYNITRIDE

BACKGROUND OF THE INVENTION

5 Field of the Invention

This invention relates to a treatment on a silicon oxynitride, and more particularly, relates to a treatment of removing the silicon oxynitride.

Description of the Related Art

10 Silicon oxynitride (SiON) is often used on a polysilicon gate as an anti-reflection layer. A silicon oxynitride layer is a silicon rich film comprising many dangling bonds on the surface. Such a surface tends to form a layer of silicon dioxide (SiO₂) when the surface is exposed to oxygen free radicals (O-*). For example, as a photo resist layer on a surface of a silicon oxynitride layer is removed by means of
15 oxygen plasma, SiO₂ is formed on the surface of the SiON layer. As a result, it is difficult to remove the silicon oxynitride layer, which lies underneath the silicon dioxide, by phosphoric acid in a latter segment of the process.

Figure 1 depicts a molecular structure of a surface of a SiON layer, which comprises many dangling bonds 102. These dangling bonds 102 react easily with the
20 oxygen free radicals in the surrounding to form a layer of SiO₂ on the surface of the SiON layer. The SiO₂ layer 202 covering the SiON layer 200 is illustrated in Figure 2.

Although the phosphoric acid is very effective in removing the silicon oxynitride, it is rather ineffective in removing the silicon dioxide. Hence, it is difficult to remove the silicon oxynitride layer 200 located underneath the silicon dioxide layer 202 using

the phosphoric acid, and is often resulted with silicon oxynitride residues.

A photo resist layer on a SiON layer is conventionally removed by an etching with oxygen plasma to the endpoint. An overetch is further conducted to completely remove the photo resist layer. A disadvantage with this approach is the oxygen plasma
5 provides a source of oxygen and easily leads to a formation of a SiO₂ layer on the surface of the SiON layer.

SUMMARY OF THE INVENTION

Accordingly, this invention provides a treatment on a silicon oxynitride surface,
10 which is also applicable to a removal of a silicon oxynitride layer covered by a photo resist layer. Oxygen plasma is used to remove a majority of the photo resist layer, followed by an overetch using non-oxygen plasma to remove a residual of the photo resist layer.

Inert gas plasma is preferred for the non-oxygen plasma; and argon plasma is
15 preferred among the inert gas plasma. The duration of the overetch is preferably in the vicinity of about 20% to about 25% of the duration of the oxygen plasma etching process.

The current invention also provides a method to remove a silicon oxide material, wherein the silicon oxide material is resulted from a reaction between silicon containing
20 materials and oxygen plasma. By means of an ion bombardment method, the inert gas plasma is used to treat the silicon oxide material, and the inert gas plasma is preferred to be argon plasma.

The current invention also provides a method to remove a photo resist layer. The method is applicable in a removal of a photo resist layer covering a layer of silicon

oxynitride. Oxygen plasma is used to remove a majority of the photo resist layer, followed by an overetch using non-oxygen plasma to remove a residual of the photo resist layer.

Inert gas plasma is preferred for the non-oxygen plasma; and the inert gas
5 plasma is preferred to be argon plasma. The duration for the overetch is preferably in a vicinity of about 20% to about 25% of the duration of the oxygen plasma etching process.

The foregoing general descriptions are exemplary only, other additional advantages of the current invention are further disclosed in the following embodiment.

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BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings illustrate presently the preferred embodiments of the invention and together with the general description given above and the detailed description of the preferred embodiment given below, serve to explain the principles of
15 the invention.

Figure 1 is a diagram illustrating the molecular structure of a surface of a SiON layer;

Figure 2 is a schematic diagram showing a silicon oxynitride layer covered by a silicon dioxide (SiO_2) layer;

20 Figure 3A to 3B are schematic diagrams showing the progression of a method for treating a silicon oxynitride surface; and

Figures 4 is a schematic diagram showing the formation of a SiO_2 layer resulted from an oxygen plasma overetching process.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

As shown in Figure 3A, a photo resist layer 302 covers a silicon oxynitride (SiON) layer 300. The SiON layer 300 can be an anti-reflection layer on a polysilicon gate. Since the anti-reflection layer is removed in a latter segment of a semiconductor manufacturing process, the susceptibility of the anti-reflection layer to a phosphoric acid removal is very important.

Still referring to Figure 3A, the arrows 304 in the figure indicate an oxygen plasma treatment process is being conducted as a first etching step of the photo resist layer 302. The endpoint of the etching process is normally defined at a point above the SiON layer. Although it is possible to control the endpoint for the etching process, a silicon oxide material, such as silicon dioxide, may be formed on the silicon oxynitride layer 300 during the oxygen plasma treatment process. Since it is difficult to control the endpoint of the etching process, even with a majority of the photo resist layer 302 being removed, a second etching step is required to remove a residual of the photo resist layer 302.

Referring to Figure 3B, arrows 306 in the figure indicate a non-oxygen plasma treatment process is being conducted, wherein the non-oxygen plasma includes inert gas plasma, and preferably argon plasma. This treatment, which is regarded as a second etching step for the photo resist layer, is an overetch to completely remove the photo resist layer 302 (as in Figure 3A). The duration of the overetch is approximately 20% to 25% of that of the first etching step. Furthermore, the non-oxygen plasma treatment process does not lead to a formation of a silicon oxide material, such as silicon dioxide, on the SiON layer. Besides being used to overetch, the non-oxygen plasma treatment process possesses other advantages. For example, by means of an ion bombardment

method, the silicon oxide material produced from an oxygen plasma treatment process is removed. As a result of removing the silicon oxide material, the SiON layer 300 is easily removed by the phosphoric acid in a latter segment of the semiconductor manufacturing process.

5 It is important to note that if oxygen plasma is used for the overetch, the effect of this invention is not accomplished because a silicon dioxide layer 308 is formed on the SiON layer, as indicated in Figure 4. This SiO₂ layer 308 is difficult to remove; therefore it is also problematic in removing the underlying SiON layer 300.

 According to the current invention, using the non-oxygen plasma, for example
10 argon plasma, to overetch, not only the plasma does not promote the formation of SiO₂, it can also remove the existing SiO₂ by means of an ion bombardment.

 Additional advantages and modifications will readily occur to those skilled in the art from the consideration of the specifications and the practice of the invention disclosed herein. It is intended that the specifications and examples to be considered
15 as exemplary only, with a true scope and spirit of the invention being indicated by the following claims.